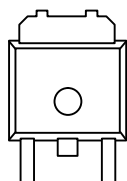


N-Channel 100 V (D-S), 150 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
100	0.0185 at $V_{GS} = 10$ V	50	48 nC

TO-252



G D S

Top View

Drain Connected to Tab

Ordering Information:

SUD50N10-18P-GE3 (Lead (Pb)-free and Halogen-free)

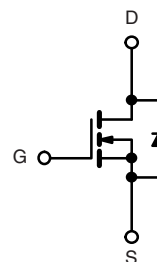
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Primary Side Switch
- Isolated DC/DC Converter



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	50 ^a	A
	$T_C = 100$ °C	33.4	
	$T_A = 25$ °C	7.8 ^b	
	$T_A = 100$ °C	5 ^b	
Pulsed Drain Current	I_{DM}	100	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	50 ^a	
	$T_A = 25$ °C	1.7 ^b	
Single Pulse Avalanche Current	I_{AS}	45	
Avalanche Energy	E_{AS}	101	mJ
Maximum Power Dissipation	$T_C = 25$ °C	113.6	W
	$T_C = 100$ °C	45.5	
	$T_A = 25$ °C	2.5 ^b	
	$T_A = 100$ °C	1 ^b	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	40	50	°C/W
Maximum Junction-to-Case	R_{thJC}	0.85	1.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

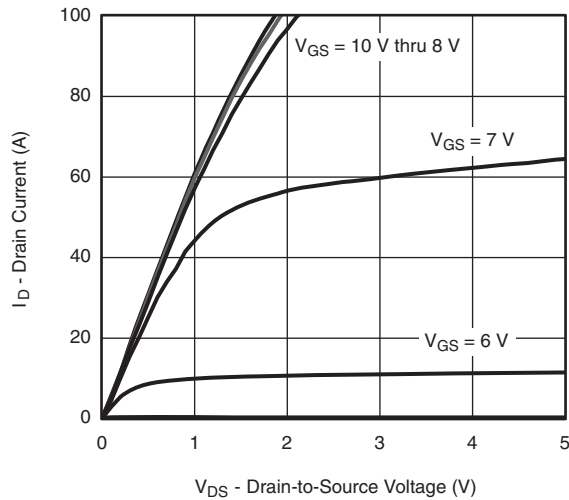
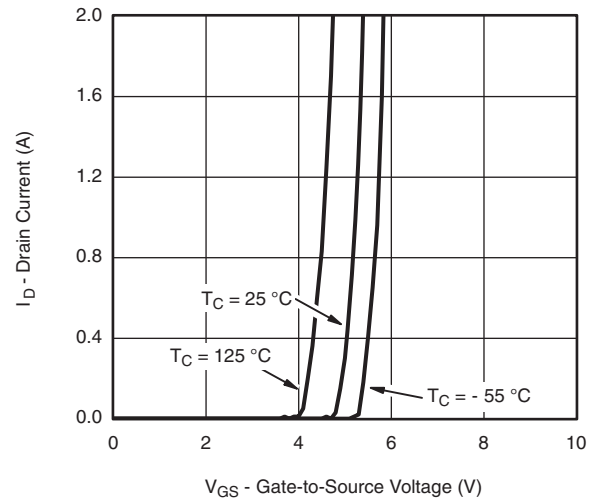
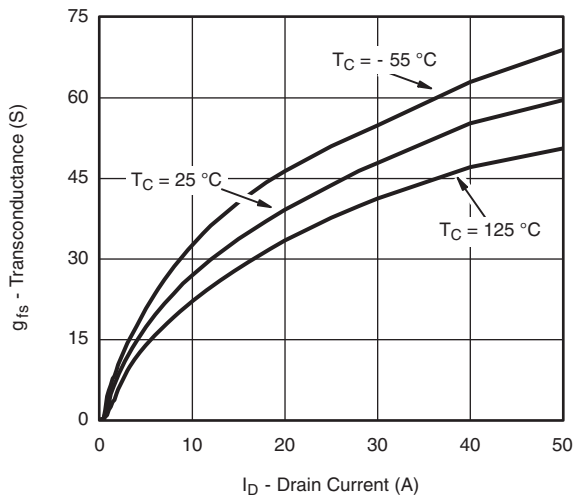
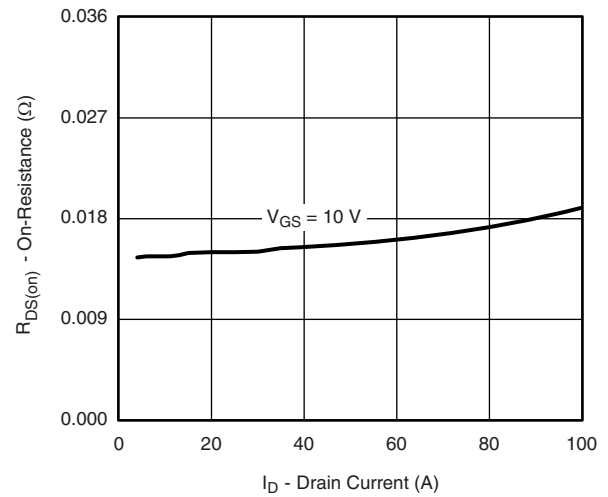
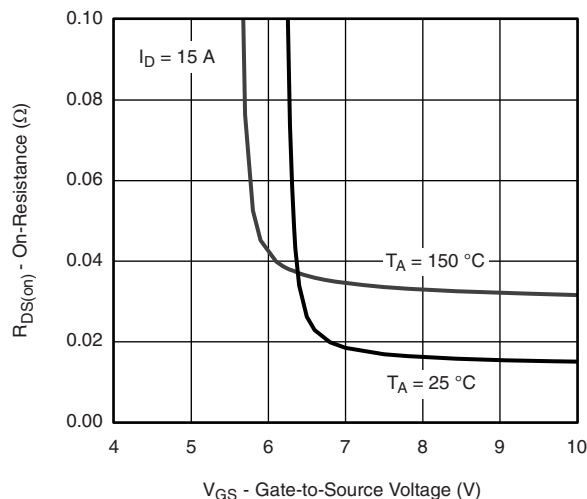
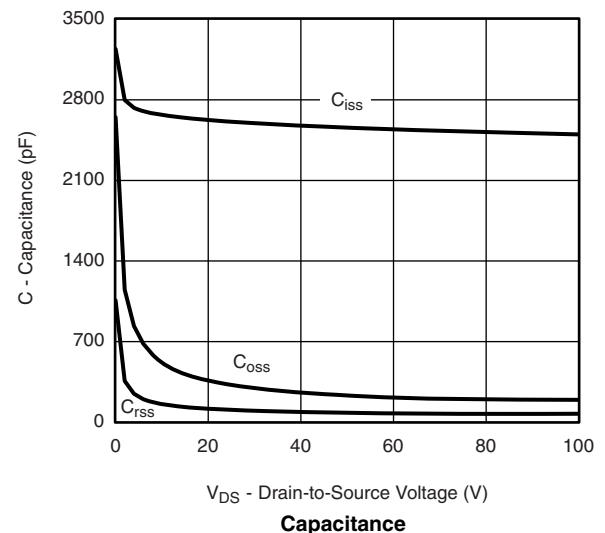
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	100			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		110		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 12.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5		5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A		0.0150	0.0185	Ω
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 15 A		33		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		2600		pF
Output Capacitance	C _{oss}			230		
Reverse Transfer Capacitance	C _{rss}			80		
Total Gate Charge	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 50 A		48	75	nC
Gate-Source Charge	Q _{gs}			16		
Gate-Drain Charge	Q _{gd}			13		
Gate Resistance	R _g	f = 1 MHz		1.6	2.5	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 1 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 1 Ω		12	20	ns
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			18	35	
Fall Time	t _f			8	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode	I _S	T _C = 25 °C			50	A
Pulse Diode Forward Current ^a	I _{SM}				100	
Body Diode Voltage	V _{SD}	I _S = 15 A		0.85	1.5	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 50 A, dI/dt = 100 A/μs, T _J = 25 °C		80	120	ns
Body Diode Reverse Recovery Charge	Q _{rr}			160	240	nC
Reverse Recovery Fall Time	t _a			57		ns
Reverse Recovery Rise Time	t _b			23		

Notes:

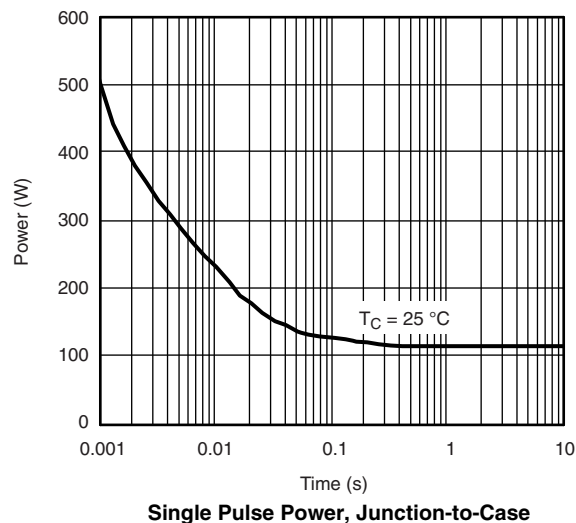
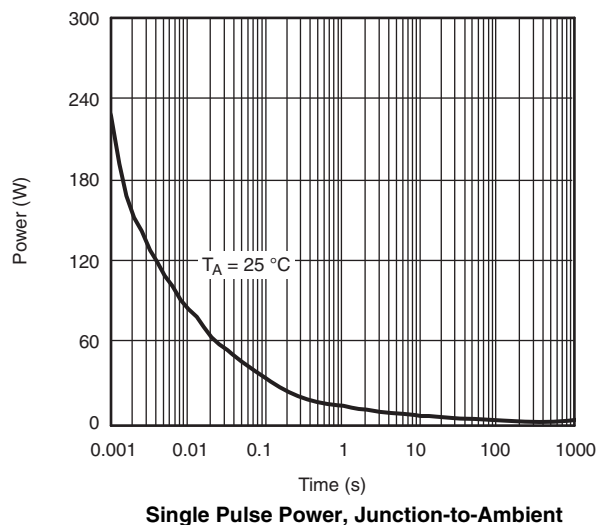
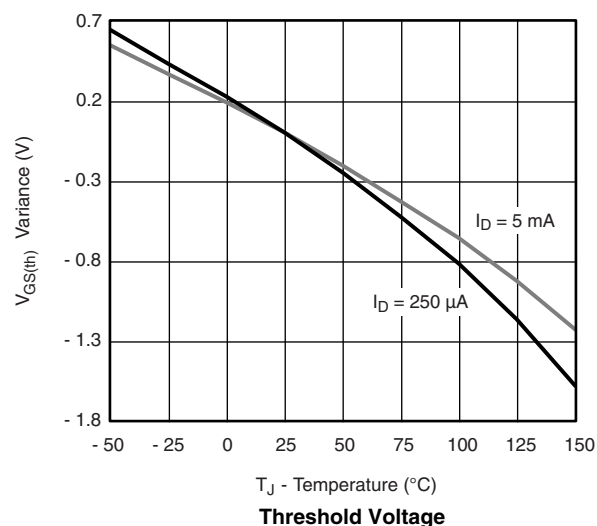
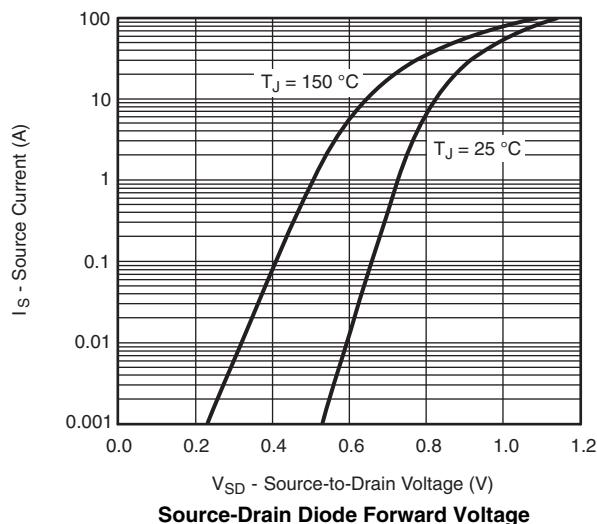
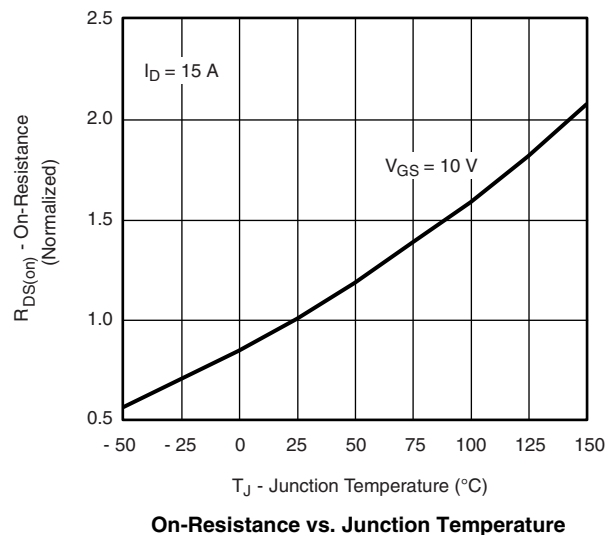
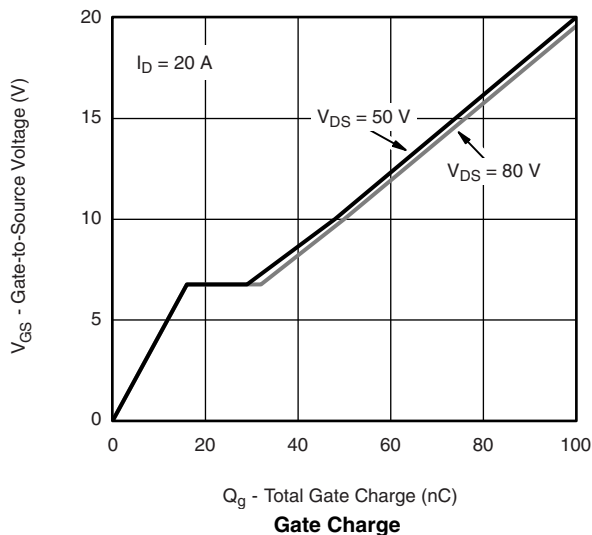
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

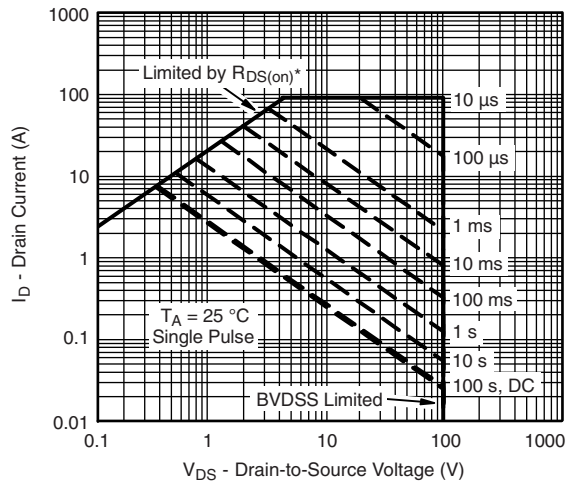
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

On-Resistance vs. Gate-to-Source Voltage

Capacitance

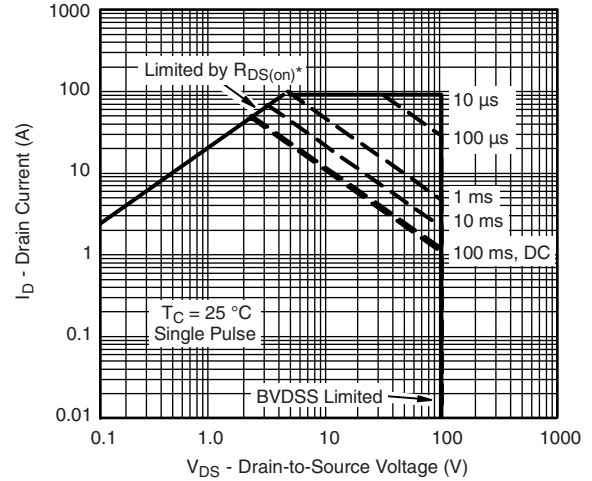
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



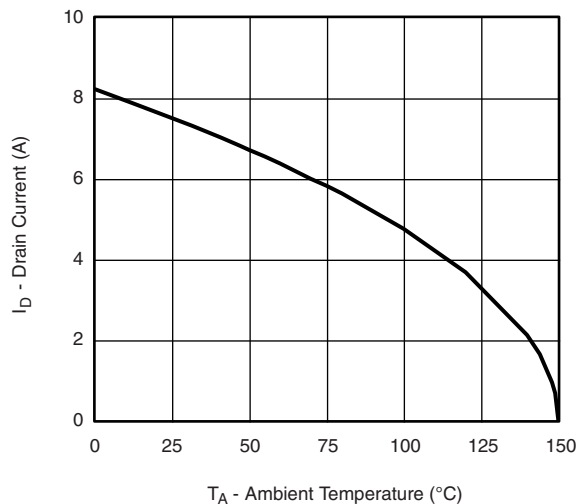
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



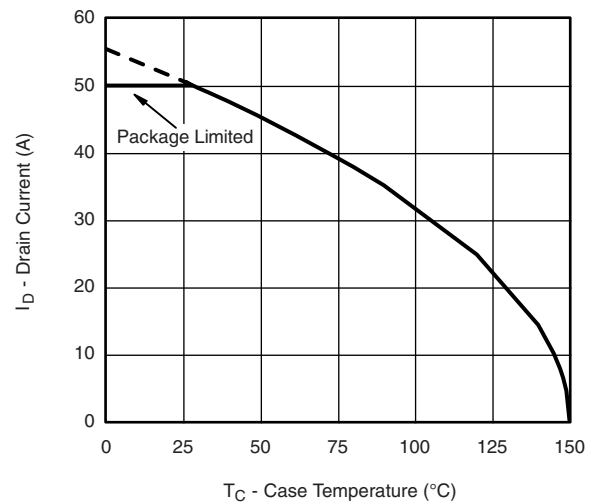
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Case

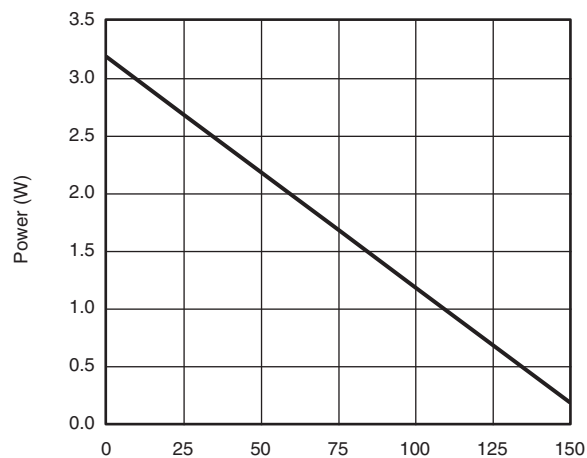


Current Derating, Junction-to-Ambient**

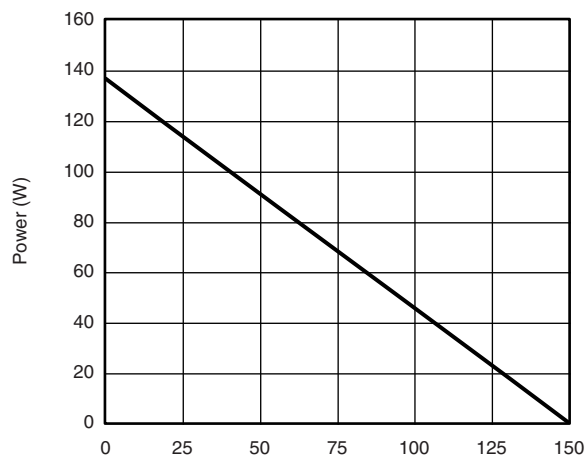


Current Derating, Junction-to-Case**

** The power dissipation P_D is based on $T_{J(max)} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

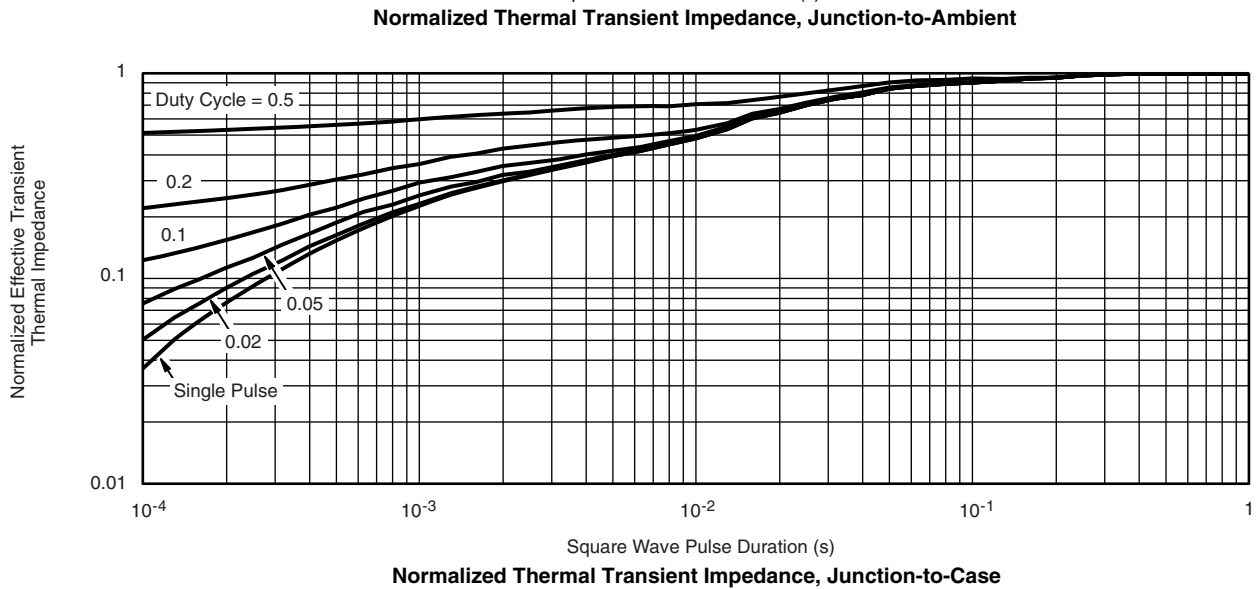
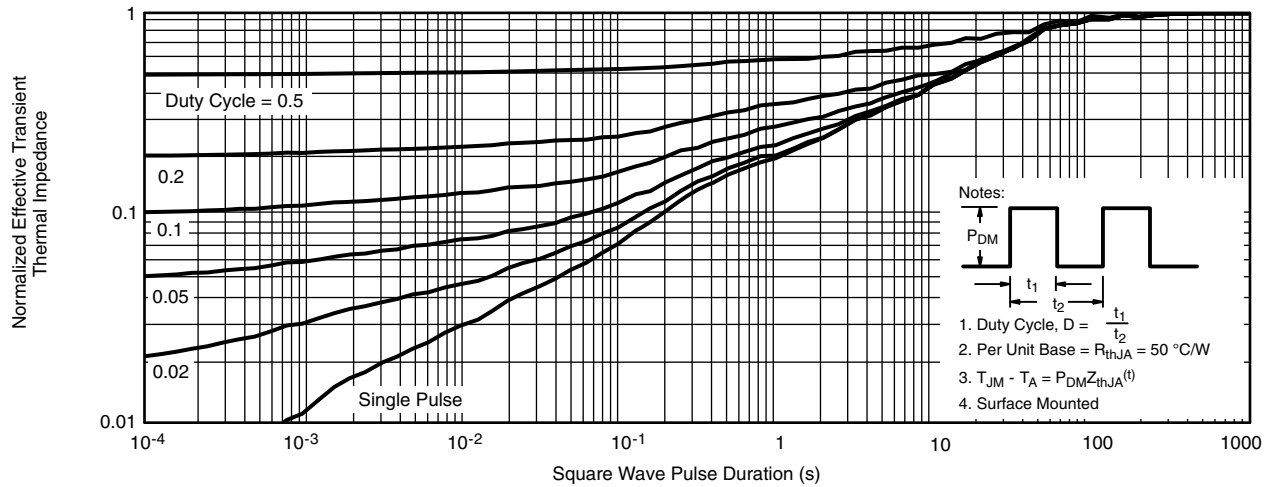
T_A - Ambient Temperature (°C)
Power Derating, Junction-to-Ambient**



T_C - Case Temperature (°C)
Power Derating, Junction-to-Case**

** The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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